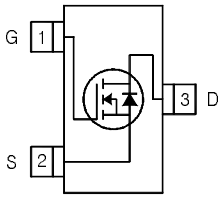
International
IOR Rectifier

PD - 96163

IRLML2502GPbF

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- N-Channel MOSFET
- SOT-23 Footprint
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching
- Lead-Free
- Halogen-Free



V_{DSS} = 20V

$R_{DS(on)}$ = 0.045Ω

Description

These N-Channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET® power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in battery and load management.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.

Micro3™

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	20	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 4.5V	4.2	A
I_D @ T_A= 70°C	Continuous Drain Current, V_{GS} @ 4.5V	3.4	
I_{DM}	Pulsed Drain Current ①	33	
P_D @T_A = 25°C	Power Dissipation	1.25	W
P_D @T_A = 70°C	Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/°C
V_{GS}	Gate-to-Source Voltage	± 12	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	75	100	°C/W

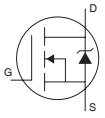
07/22/08

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.01	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.035	0.045	Ω	V_{GS} = 4.5V, I_D = 4.2A ②
		—	0.050	0.080		V_{GS} = 2.5V, I_D = 3.6A ②
$V_{GS(th)}$	Gate Threshold Voltage	0.60	—	1.2	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	5.8	—	—	S	V_{DS} = 10V, I_D = 4.0A
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	µA	V_{DS} = 16V, V_{GS} = 0V
		—	—	25		V_{DS} = 16V, V_{GS} = 0V, T_J = 70°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V_{GS} = -12V
	Gate-to-Source Reverse Leakage	—	—	100		V_{GS} = 12V
Q_g	Total Gate Charge	—	8.0	12	nC	I_D = 4.0A
Q_{gs}	Gate-to-Source Charge	—	1.8	2.7		V_{DS} = 10V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	1.7	2.6		V_{GS} = 5.0V ②
$t_{d(on)}$	Turn-On Delay Time	—	7.5	—	ns	V_{DD} = 10V
t_r	Rise Time	—	10	—		I_D = 1.0A
$t_{d(off)}$	Turn-Off Delay Time	—	54	—		R_G = 6Ω
t_f	Fall Time	—	26	—		R_D = 10Ω ②
C_{iss}	Input Capacitance	—	740	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	90	—		V_{DS} = 15V
C_{rss}	Reverse Transfer Capacitance	—	66	—		f = 1.0MHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	1.3	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	33		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	T_J = 25°C, I_S = 1.3A, V_{GS} = 0V ②
t_{rr}	Reverse Recovery Time	—	16	24	ns	T_J = 25°C, I_F = 1.3A
Q_{rr}	Reverse Recovery Charge	—	8.6	13	nC	di/dt = 100A/µs ②



Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Pulse width ≤ 300µs; duty cycle ≤ 2%.

③ Surface mounted on FR-4 board, t ≤ 5sec.

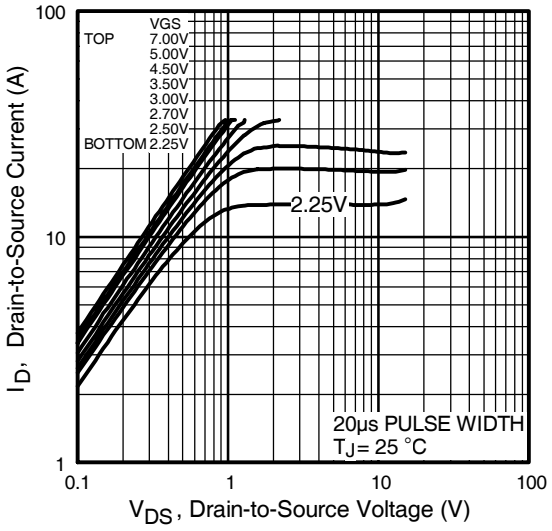


Fig 1. Typical Output Characteristics

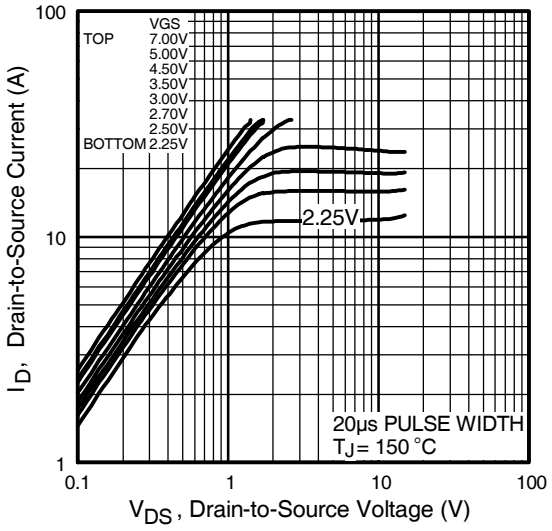


Fig 2. Typical Output Characteristics

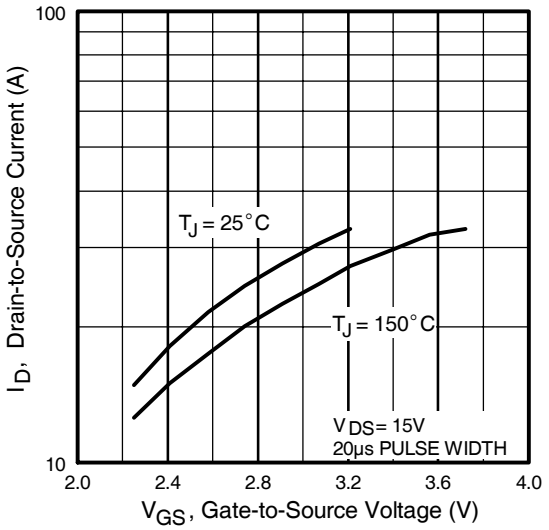


Fig 3. Typical Transfer Characteristics

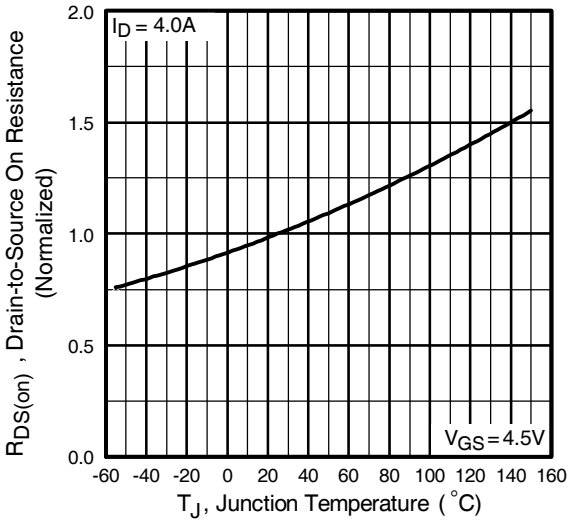


Fig 4. Normalized On-Resistance Vs. Temperature

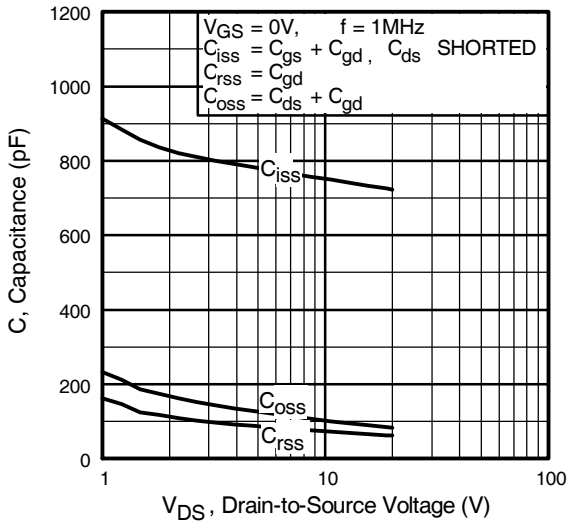


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

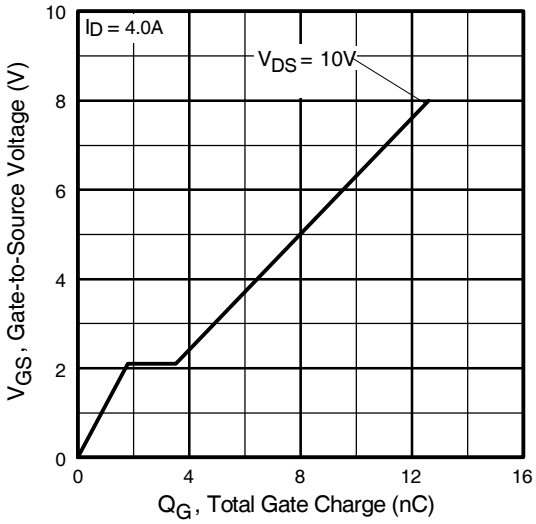


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

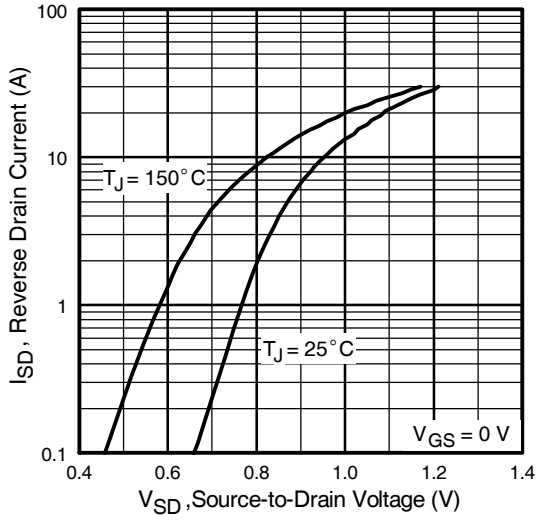


Fig 7. Typical Source-Drain Diode Forward Voltage

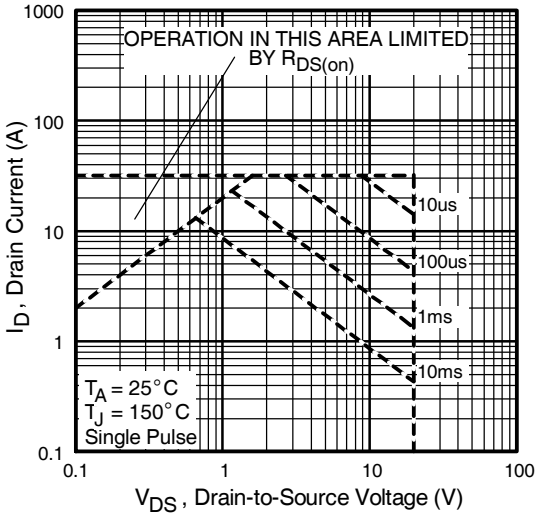


Fig 8. Maximum Safe Operating Area

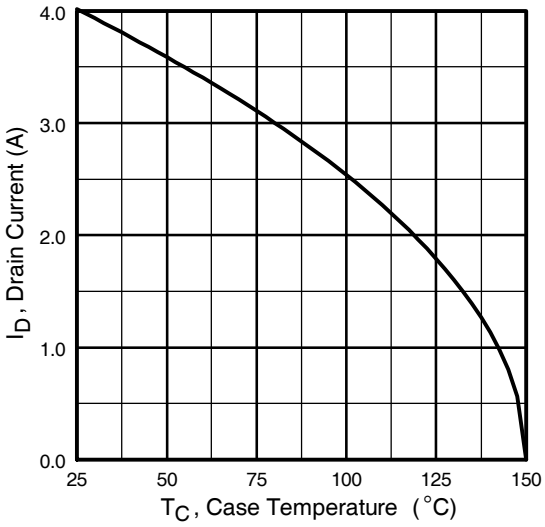


Fig 9. Maximum Drain Current Vs. Case Temperature

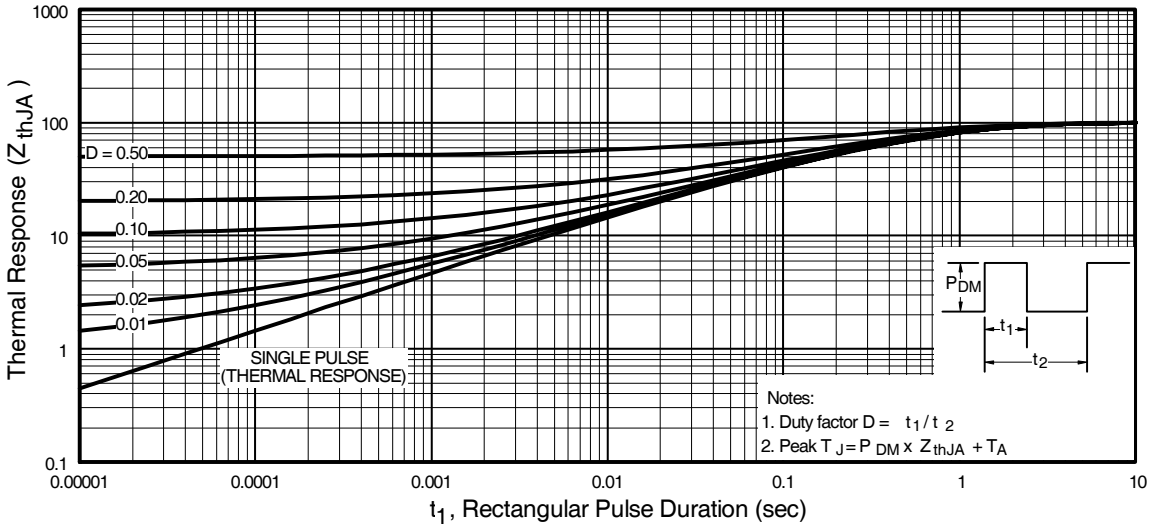


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

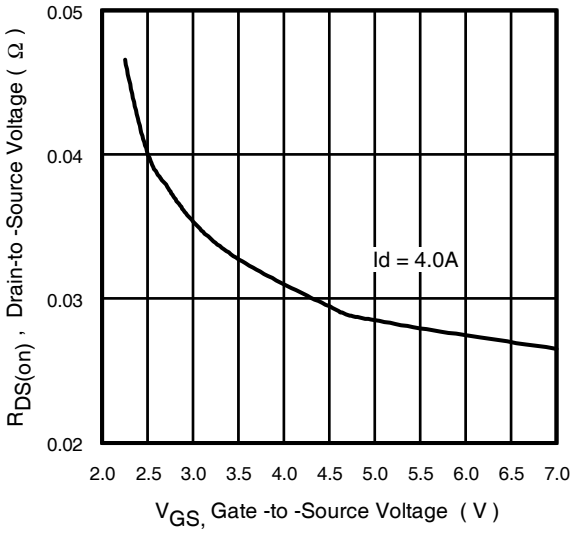


Fig 11. On-Resistance Vs. Gate Voltage

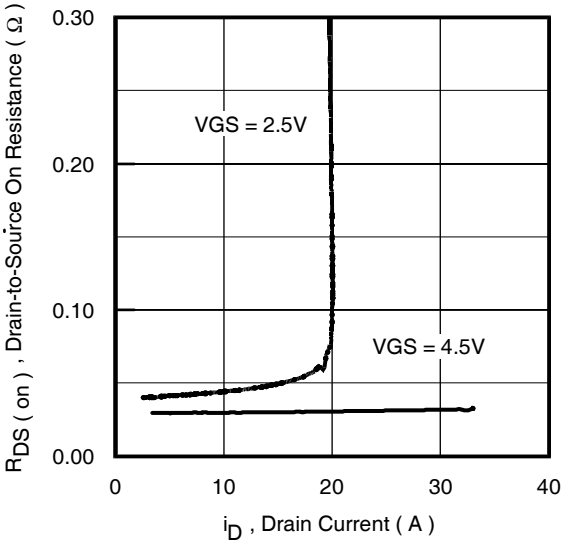
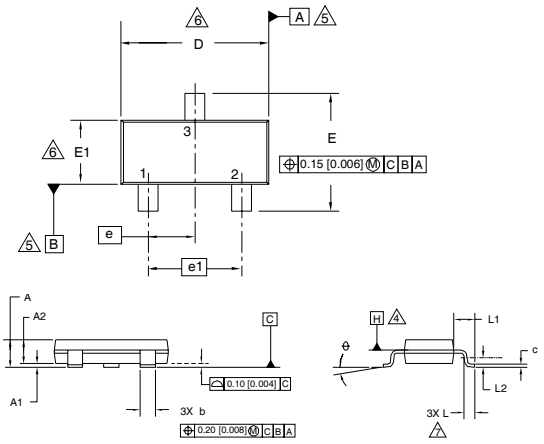


Fig 12. On-Resistance Vs. Drain Current

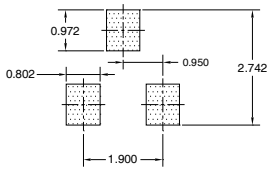
Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



DIMENSIONS				
SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.89	1.12	0.035	0.044
A1	0.01	0.10	0.0004	0.004
A2	0.88	1.02	0.035	0.040
b	0.30	0.50	0.012	0.020
c	0.08	0.20	0.003	0.008
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E1	1.20	1.40	0.047	0.055
e	0.95	BSC	0.037	BSC
e1	1.90	BSC	0.075	BSC
L	0.40	0.60	0.016	0.024
L1	0.54	REF	0.021	REF
L2	0.25	BSC	0.010	BSC
θ	0	8	0	8

Recommended Footprint

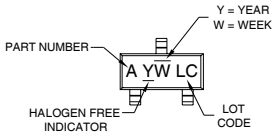


NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. CONTROLLING DIMENSION: MILLIMETER.
4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H. DIMENSIONS DOES NOT INCLUDE MOLD PROTRUSIONS OR INTERLEAD FLASH. MOLD PROTRUSIONS OR INTERLEAD FLASH SHALL NOT EXCEED 0.25 MM [0.010 INCH] PER SIDE.
7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236 AB.

Micro3 (SOT-23 / TO-236AB) Part Marking Information

Micro3 / SOT-23 Package Marking



PART NUMBER CODE REFERENCE:

A = IRLML2402
B =IRLML2803
C = IRLML2402
D = IRLML5103
E = IRLML6402
F = IRLML6401
G = IRLML2502
H = IRLML5203

Note: A line above the work week
(as shown here) indicates Lead-free

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
2006	6		
2007	7		
2008	8		
2009	9		
2010	0	24	X
		25	Y
		26	Z

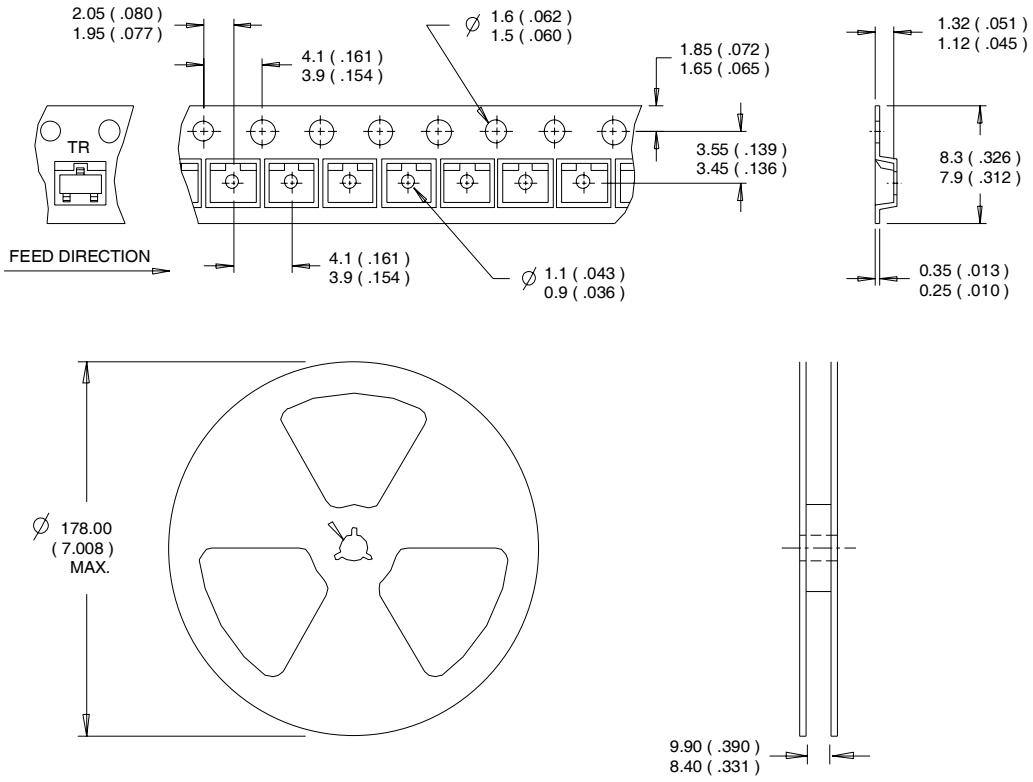
W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
2006	F		
2007	G		
2008	H		
2009	J		
2010	K	50	X
		51	Y
		52	Z

Note: For the most current drawing please refer to IR website at http://www.irf.com/package

Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package

Data and specifications subject to change without notice.

International
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